

a1 Additional valves, such as 43B (other valves not shown), may shut off gas from the flow controllers to the chamber.--

Please replace the paragraph beginning at line 25 of page 10 with the following rewritten paragraph:

a2 --System controller 60 operates under the control of a computer program 63 stored in a computer-readable format within memory 62. The computer program dictates the timing, temperatures, gas flows, RF power levels and other parameters of a particular process. The interface between a user and the system controller is via a CRT monitor 65 and a light pen 66, as depicted in Fig. 1C. In a preferred embodiment, two monitors, 65 and 65A, and two light pens, 66 and 66A, are used, one mounted in the clean room wall for the operators and the other behind the wall for the service technicians. Both monitors simultaneously display the same information, but only one light pen (e.g. 66) is enabled. To select a particular screen or function, the operator touches an area of the display screen and pushes a button (not shown) on the pen. The touched area confirms being selected by the light pen by changing its color or displaying a new menu, for example.--

IN THE CLAIMS:

Please add new claims 25-41 as follows.

sub B8 --25. (New) The method of claim 1 wherein the silicon oxide layer is used as a premetal dielectric layer or part of a shallow trench isolation structure.

26. (New) The method of claim 10 wherein the silicon oxide layer is used as a premetal dielectric layer or part of a shallow trench isolation structure.

a3 27. (New) The method of claim 17 wherein the silicon oxide layer is used as a premetal dielectric layer or part of a shallow trench isolation structure.

sub B9 28. (New) A method for forming a silicon oxide layer over a substrate disposed in a high density substrate processing chamber, said method comprising:  
flowing a process gas a silicon-containing source, an oxygen-containing source and a fluorine-containing source into the substrate processing chamber;